

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MC1472

**DUAL PERIPHERAL
 POSITIVE "NAND" DRIVER
 SILICON MONOLITHIC
 INTEGRATED CIRCUITS**

**DUAL PERIPHERAL-HIGH-VOLTAGE
 POSITIVE "NAND" DRIVER**

The dual driver consists of a pair of PNP buffered AND gates connected to the bases of a pair of high voltage NPN transistors. They are similar to the MC75452 drivers but with the added advantages of: 1) 70 Volt capability 2) output suppression diodes and 3) PNP buffered inputs for MOS compatibility. These features make the MC1472 ideal for mating MOS logic or microprocessors to lamps, relays, printer hammers and incandescent displays.

- 300 mA Output Capability (each transistor)
- 70 Vdc Breakdown Voltage
- Internal Output Clamp Diodes
- Low Input Loading for MOS Compatibility (PNP buffered)



**P1 SUFFIX
 PLASTIC PACKAGE
 CASE 626**

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

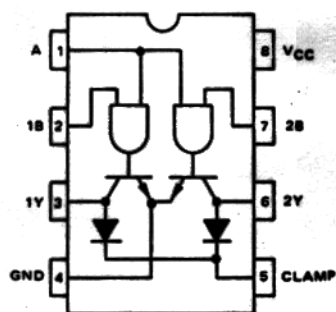
Rating	Symbol	Value	Unit
Supply Voltage	V_{CC}	7.0	V
Input Voltage	V_{in}	5.5	V
Output Voltage	V_{out}	80	V
Clamp Voltage	V_C	80	V
Output Current (Continuous)	I_O	300	mA
Operating Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

Rating	Symbol	Min	Max	Unit
Supply Voltage	V_{CC}	4.5	5.5	Volts
Operating Ambient Temperature	T_A	0	70	$^\circ\text{C}$
Output Voltage	V_O	V_{CC}	70	Volts
Clamp Voltage	V_C	V_O	70	Volts

ORDERING INFORMATION

Device	Temperature Range
	0 to +75

PIN CONNECTIONS



Positive Logic: $Y=AB^*$

TRUTH TABLE

A	B	Y
L	L	H ("OFF" STATE)
L	H	
H	L	
H	H	L ("ON" STATE)

MC1472

ELECTRICAL CHARACTERISTICS (Unless otherwise noted min/max limits apply across the 0°C to 70°C temperature range with 4.5 V ≤ V_{CC} ≤ 5.5 V. All typical values are for T_A = 25°C, V_{CC} = 5.0 Volts.)

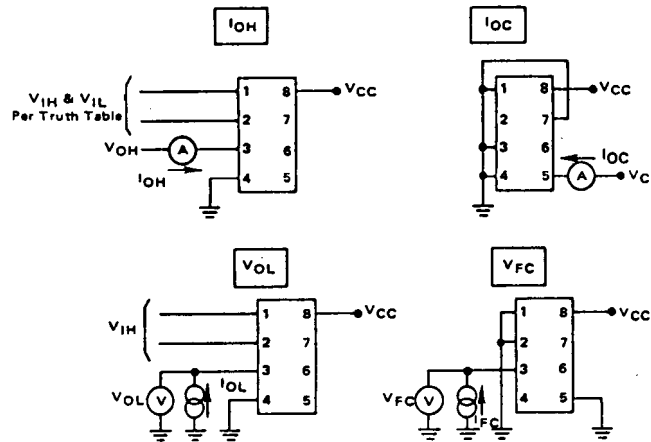
Characteristic	Symbol	Min	Typ	Max	Unit
Input Voltage — High Logic State	V _{IH}	2.0	—	5.5	V _{dc}
Input Voltage — Low Logic State	V _{IL}	0	—	0.8	V _{dc}
Input Current — Low Logic State (V _{IL} = 0.4 V) A Input B Input	I _{IL}	—	—	−0.3 −0.15	mA
Input Current — High Logic State (V _{IH} = 2.4 V) A Input B Input (V _{IH} = 5.5 V) A Input B Input	I _{IH}	— — — —	— — — —	40 20 200 100	μA
Input Clamp Voltage (I _{CC} = −12 mA)	V _{IK}	—	—	−1.5	V
Output Leakage Current — High Logic State (V _O = 70 V, See Test Figure)	I _{OH}	—	—	100	μA
Output Voltage — Low Logic State (I _{OL} = 100 mA) (I _{OL} = 300 mA)	V _{OL}	— —	— —	0.4 0.7	V
Output Clamp Diode Leakage Current (V _C = 70 V, See Test Figure)	I _{OC}	—	—	100	V
Output Clamp Forward Voltage (I _{FC} = 300 mA, See Test Figure)	V _{FC}	—	—	1.7	V
Power Supply Current (All Inputs at V _{IH}) (All Inputs at V _{IL})	I _{CC}	— —	— —	70 15	mA

NOTE: All currents into device pins are shown as positive, out of device pins as negative. All voltages referenced to ground unless otherwise noted.

SWITCHING CHARACTERISTICS V_{CC} = 5.0V, T_A = 25°C

Characteristic	Symbol	Min	Typ	Max	Unit
Propagation Delay Time Output High to Low Output Low to High	t _{PHL} t _{PLH}	— —	— —	1.0 0.75	μs
Output Transition Time Output High to Low Output Low to High	t _{THL} t _{TLH}	— —	— —	0.1 0.1	μs

TEST CIRCUITS



SWITCHING TEST CIRCUIT AND WAVEFORM

